

SavantIC Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD884

DESCRIPTION

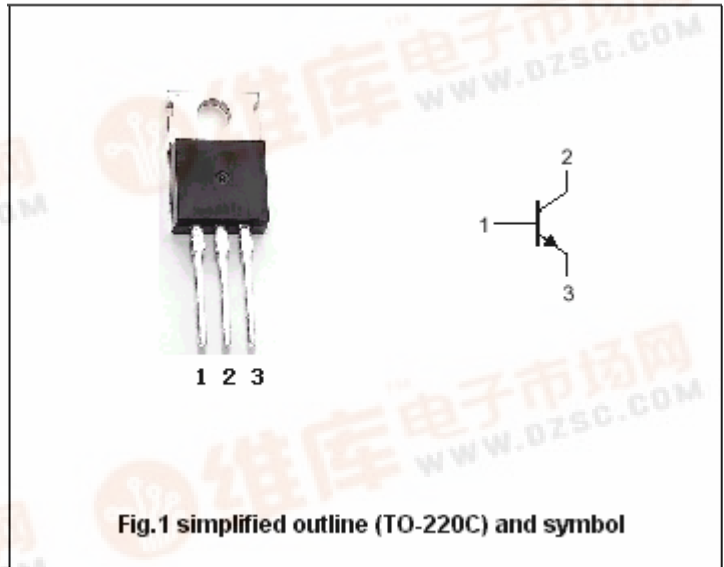
- With TO-220C package
- High voltage;high speed
- Large  $P_C$

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS( $T_C=25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	330	V
$V_{CEO}$	Collector-emitter voltage	Open base	200	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		7	A
$I_{CP}$	Collector current-Peak		10	A
$I_{CP}$	Collector current-Peak	nonrepetitive	15	A
$P_T$	Total power dissipation	$T_C=25^\circ C$	40	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	200			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			1.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			1.2	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =330V; V <sub>EB</sub> =0			0.1	mA
		V <sub>CE</sub> =300V; V <sub>EB</sub> =0, T <sub>a</sub> =100°C			1.0	
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6.0V; I <sub>C</sub> =0			1.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =4V	10		45	
t <sub>f</sub>	Fall time	I <sub>C</sub> =5A ; -V <sub>EB</sub> =5V I <sub>B1</sub> =0.8A; R <sub>B</sub> =0.5Ω			0.75	μs

PACKAGE OUTLINE

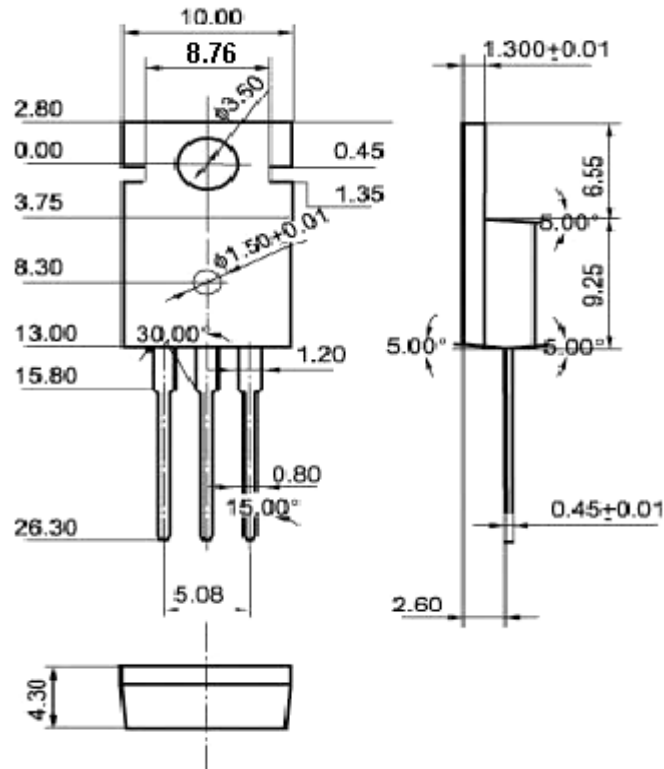


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)